

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

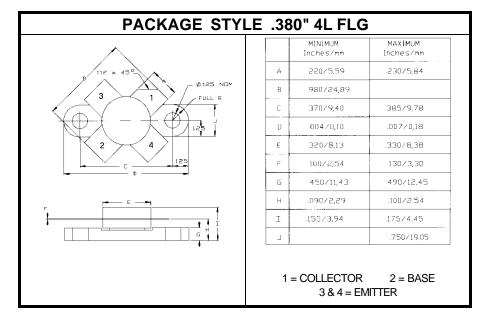
The **ASI S15-28** is Designed for Class AB or C, Common Emitter Linear HF Communications Applications.

FEATURES INCLUDE:

 High Power Gain Emitter Ballasting

MAXIMUM RATINGS

Ιc	3.0 A
V _{CB}	65 V
P _{DISS}	$30 \text{ W} @ \text{T}_{\text{C}} = 25 \ ^{\text{O}}\text{C}$
TJ	-55 ^o C to +200 ^o C
T _{STG}	-55 ^o C to +200 ^o C
T IC	5.8 ^O C/W



CHARACTERISTICS $T_c = 25 °C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CBO}	I _C = 200 mA			65			V
BV _{CEO}	I _C = 200 mA			35			V
BV _{EBO}	l _E = 10 mA			4.0			V
І _{сво}	V _{CB} = 30 V					1.0	mA
h _{FE}	$V_{CE} = 5.0 \text{ V}$ $I_{C} = 20$	00 mA		10			
C _{ob}	V _{CB} = 30 V	f = 1	.0 MHz			35	pF
P _{out} P _g M _c	$V_{CE} = 28 V$ $P_{in} = 5$	00 mW fo = 3	30 MHz	15 15 	 18 65		W dB %

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REV. A

Specifications are subject to change without notice.